

# Alexander A Lebedev

## List of Publications by Citations

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357  
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376  
ext. papers

2,390  
ext. citations

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avg, IF

5.03  
L-index

#	Paper	IF	Citations
357	Deep level centers in silicon carbide: A review. <i>Semiconductors</i> , <b>1999</b> , 33, 107-130	0.7	196
356	Influence of phase transformations on the mechanical properties of austenitic stainless steels. <i>International Journal of Plasticity</i> , <b>2000</b> , 16, 749-767	7.6	138
355	Heterojunctions and superlattices based on silicon carbide. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, R17-R34	1.8	132
354	Doping of n-type 6H-SiC and 4H-SiC with defects created with a proton beam. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 6265-6271	2.5	88
353	Wide-gap semiconductors for high-power electronics. <i>Semiconductors</i> , <b>1999</b> , 33, 999-1001	0.7	43
352	Radiation Resistance of SiC and Nuclear-Radiation Detectors Based on SiC Films. <i>Semiconductors</i> , <b>2004</b> , 38, 125	0.7	42
351	Low-doped 6H-SiC n-type epilayers grown by sublimation epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 77, 50-54	3.1	40
350	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). <i>Semiconductors</i> , <b>2017</b> , 51, 1072-1080	0.7	33
349	Effect of Annealing on Defects in As-Grown and $\beta$ Ray Irradiated n-GaN Layers. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 216, 533-536	1.3	32
348	Radiation hardness of wide-gap semiconductors (using the example of silicon carbide). <i>Semiconductors</i> , <b>2002</b> , 36, 1270-1275	0.7	31
347	Similarities and distinctions of defect production by fast electron and proton irradiation: Moderately doped silicon and silicon carbide of n-type. <i>Semiconductors</i> , <b>2012</b> , 46, 456-465	0.7	26
346	Graphene Nanoribbons for Electronic Devices. <i>Annalen Der Physik</i> , <b>2017</b> , 529, 1700033	2.6	24
345	Process induced deep-level defects in high purity silicon. <i>Semiconductor Science and Technology</i> , <b>1998</b> , 13, 488-495	1.8	24
344	Fabrication of SiC epitaxial structures for devices by the method of sublimation in an open system. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1992</b> , 11, 113-115	3.1	24
343	Model for conductivity compensation of moderately doped n- and p-4H-SiC by high-energy electron bombardment. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 155702	2.5	22
342	4H-SiC IMPATT Diode Fabrication and Testing. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 1353-1358	0.4	20
341	Radiation hardness of SiC based ions detectors for influence of the relative protons. <i>Applied Surface Science</i> , <b>2001</b> , 184, 431-436	6.7	19

340	Electrical characteristics of p-3C <sub>SiC</sub> /n-6H <sub>SiC</sub> heterojunctions grown by sublimation epitaxy on 6H <sub>SiC</sub> substrates. <i>Applied Surface Science</i> , <b>2001</b> , 184, 419-424	6.7	19
339	Measurement of electrophysical properties of silicon carbide epitaxial films. <i>Diamond and Related Materials</i> , <b>1994</b> , 3, 1393-1397	3.5	19
338	New results in sublimation growth of the SiC epilayers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 165-167	3.1	18
337	Effect of boron diffusion on the high-voltage behavior of 6H-SiC p+nn+ structures. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 5464-5468	2.5	18
336	Impact of high energy electron irradiation on high voltage Ni/4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 083503	3.4	17
335	Electrical and noise properties of proton irradiated 4H-SiC Schottky diodes. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 024502	2.5	16
334	Radiation-stimulated photoluminescence in electron irradiated 4H-SiC. <i>Journal Physics D: Applied Physics</i> , <b>2015</b> , 48, 485106	3	16
333	Effect of electron irradiation on carrier removal rate in silicon and silicon carbide with 4H modification. <i>Semiconductors</i> , <b>2008</b> , 42, 242-247	0.7	16
332	Graphene-based biosensors. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 729-732	0.7	14
331	Low-temperature transport properties of multigraphene films grown on the SiC surface by sublimation. <i>Semiconductors</i> , <b>2011</b> , 45, 623-627	0.7	14
330	Highly doped p-type 3C <sub>SiC</sub> on 6H <sub>SiC</sub> substrates. <i>Semiconductor Science and Technology</i> , <b>2008</b> , 23, 075004	1.8	14
329	DLTS study of defects in 6H- and 4H-SiC created by proton irradiation. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 641-644	2.8	14
328	Radiation defects in n-6H-SiC irradiated with 8 MeV protons. <i>Semiconductors</i> , <b>2000</b> , 34, 861-866	0.7	14
327	Investigation of 3C-SiC Epitaxial Layers Grown by Sublimation Epitaxy. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 221-224	0.4	14
326	Metal-6H <sub>SiC</sub> surface barrier height: Experimental data and description in the traditional terms. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 5511-5514	2.5	14
325	Supersensitive graphene-based gas sensor. <i>Technical Physics</i> , <b>2016</b> , 61, 453-457	0.5	14
324	Irradiation of 4H-SiC UV detectors with heavy ions. <i>Semiconductors</i> , <b>2015</b> , 49, 540-546	0.7	13
323	Charge carrier removal rates in n-type silicon and silicon carbide subjected to electron and proton irradiation. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4752-4754	2.8	13

322	Formation of nanocarbon films on the SiC surface through sublimation in vacuum. <i>Physics of the Solid State</i> , <b>2009</b> , 51, 829-832	0.8	13
321	A study of thick 3C-SiC epitaxial layers grown on 6H-SiC substrates by sublimation epitaxy in vacuum. <i>Semiconductors</i> , <b>2007</b> , 41, 263-265	0.7	13
320	Transport of the charge carriers in SiC-detector structures after extreme radiation fluences. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2006</b> , 569, 758-763	1.2	13
319	Surface barrier height in metal-n-6H-SiC structures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1995</b> , 29, 198-201	3.1	13
318	Radiation Effects in Silicon Carbide. <i>Materials Research Foundations</i> , <b>2017</b> ,	1.3	13
317	Influence of the defect density (twins boundaries) on electrical parameters of 3C-SiC epitaxial films. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4758-4760	2.8	12
316	Features of the structure of a porous silicon carbide layer obtained by electrochemical etching of a 6H-SiC substrate. <i>Technical Physics Letters</i> , <b>2002</b> , 28, 935-938	0.7	12
315	Study of multigraphene films prepared by sublimation on the sic surface. <i>Physics of the Solid State</i> , <b>2010</b> , 52, 855-861	0.8	11
314	A vacancy model of the heteropolytype epitaxy of SiC. <i>Semiconductors</i> , <b>2005</b> , 39, 277-280	0.7	11
313	Investigation of the structure of (p)3C-SiC-(n)6H-SiC heterojunctions. <i>Technical Physics Letters</i> , <b>2001</b> , 27, 1052-1054	0.7	11
312	Effect of irradiation with MeV protons and electrons on the conductivity compensation and photoluminescence of moderately doped p-4H-SiC (CVD). <i>Semiconductors</i> , <b>2015</b> , 49, 1163-1165	0.7	10
311	Size confinement effect in graphene grown on 6H-SiC (0001) substrate. <i>Carbon</i> , <b>2015</b> , 86, 139-145	10.4	10
310	Structure and transport properties of nanocarbon films prepared by sublimation on a 6H-SiC surface. <i>Semiconductors</i> , <b>2013</b> , 47, 301-306	0.7	10
309	Radiation resistance of transistor-and diode-type SiC detectors irradiated with 8-MeV protons. <i>Semiconductors</i> , <b>2004</b> , 38, 807-811	0.7	10
308	Role of the recoil atom energy in the formation of radiation-induced defects in semiconductors under electron bombardment. <i>Journal of Surface Investigation</i> , <b>2015</b> , 9, 231-236	0.5	9
307	Intercalation of Iron Atoms under Graphene Formed on Silicon Carbide. <i>Physics of the Solid State</i> , <b>2018</b> , 60, 1439-1446	0.8	9
306	Conductivity compensation in n-4H-SiC (CVD) under irradiation with 0.9-MeV electrons. <i>Semiconductors</i> , <b>2014</b> , 48, 1006-1009	0.7	9
305	Formation of Periodic Steps on 6H-SiC (0001) Surface by Annealing in a High Vacuum. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 437-440	0.4	9

304	Comparative study of changes in electrical properties of silicon and silicon carbide upon proton irradiation. <i>Semiconductors</i> , <b>2010</b> , 44, 678-684	0.7	9
303	Carrier Removal in Electron Irradiated 4H and 6H SiC. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 425-428	0.4	9
302	Effect of elevated temperatures (up to 250°C) on the operating capacity of heavily irradiated p+n SiC detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2008</b> , 597, 203-206	1.2	9
301	Simulation and Prototype Fabrication of Microwave Modulators with 4H-SiC p-i-n Diodes. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1089-1092	0.4	9
300	The effect of low-energy ion bombardment on the density and crystal structure of thin films. <i>Technical Physics</i> , <b>2001</b> , 46, 1020-1025	0.5	9
299	Radiation defects in n-4H-SiC irradiated with 8-MeV protons. <i>Semiconductors</i> , <b>2000</b> , 34, 1016-1020	0.7	9
298	Influence of native defects on polytypism in SiC. <i>Semiconductors</i> , <b>1999</b> , 33, 707-709	0.7	9
297	Effect of high energy electron irradiation on low frequency noise in 4H-SiC Schottky diodes. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 133501	3.4	8
296	Nonlinear effects in semiconductor-conductivity compensation by radiation defects. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 950-952	0.5	8
295	Structure and characteristics of the high-temperature SiC detectors based on Al ion-implanted p+n junctions. <i>Semiconductor Science and Technology</i> , <b>2011</b> , 26, 045001	1.8	8
294	Development of a model of silicon carbide thermodestruction for preparation of graphite layers. <i>Physics of the Solid State</i> , <b>2009</b> , 51, 481-484	0.8	8
293	Surface barrier height in metal-SiC structures of 6H, 4H and 3C polytypes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 236-239	3.1	8
292	Investigation of n-GaN/p-SiC/n-SiC heterostructures. <i>Journal of Crystal Growth</i> , <b>2007</b> , 300, 239-241	1.6	8
291	Space-charge waves in silicon carbide. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 083706	2.5	8
290	6H-SiC epilayers as nuclear particle detectors. <i>Semiconductors</i> , <b>2000</b> , 34, 243-249	0.7	8
289	Capacitance measurements for diodes in the case of strong dependence of the diode-base series resistance on the applied voltage. <i>Semiconductors</i> , <b>2000</b> , 34, 115-118	0.7	8
288	<b>2016</b> ,		7
287	6H-SiC P-N structures with predominate exciton electroluminescence, obtained by sublimation epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 275-277	3.1	7

286	Vacancy kinetics in heteropolytype epitaxy of SiC. <i>Semiconductors</i> , <b>2007</b> , 41, 621-624	0.7	7
285	Effect of extreme radiation fluences on parameters of SiC nuclear particle detectors. <i>Semiconductors</i> , <b>2006</b> , 40, 1227-1231	0.7	7
284	Microwave switches based on 4H-SiC p-i-n diodes. <i>Technical Physics Letters</i> , <b>2004</b> , 30, 123-125	0.7	7
283	Characterization of p $\bar{n}$ structures grown by sublimation heteroepitaxy of 3C-SiC on 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 91-92, 321-324 <sup>3.1</sup>	3.1	7
282	Investigation of p-3C-SiC/n <sup>+</sup> -6H-SiC Heterojunctions with Low Doped p-3C-SiC Region. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 427-430	0.4	7
281	Detection of strongly and weakly ionizing radiation by triode structure based on SiC films. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 5714-5719	2.5	7
280	On Current Limitations in Porous SiC Applications. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 269-272	0.4	7
279	The contact of metal with silicon carbide: Schottky barrier height in relation to SiC polytype. <i>Semiconductors</i> , <b>2001</b> , 35, 1375-1377	0.7	7
278	Amplification of the signal in triode structures of ion detectors based on 6H-SiC epitaxial films. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 4447-4449	3.4	7
277	Structural defects and deep-level centers in 4H-SiC epilayers grown by sublimational epitaxy in vacuum. <i>Semiconductors</i> , <b>2000</b> , 34, 1133-1136	0.7	7
276	Effect of stressed state parameters on phase transformation kinetics in austenitic steels with plastic deformation. <i>Strength of Materials</i> , <b>1989</b> , 21, 60-64	0.6	7
275	Local Anodic Oxidation of Graphene Layers on SiC. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 381-383	0.7	7
274	Anomalous Scatter of Forward Current-Voltage Characteristics of He <sup>+</sup> -Irradiated Ni/4H-SiC Schottky Diodes. <i>Materials Science Forum</i> , <b>2016</b> , 858, 749-752	0.4	6
273	Cobalt Intercalation of Graphene on Silicon Carbide. <i>Physics of the Solid State</i> , <b>2019</b> , 61, 1316-1326	0.8	6
272	Comparison of the radiation hardness of silicon and silicon carbide. <i>Semiconductors</i> , <b>2014</b> , 48, 1293-1295 <sup>0.7</sup>	0.7	6
271	Growth and investigation of epitaxial 6H-SiC layers obtained by CVD on Lely-grown substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 300-303	3.1	6
270	Instability of characteristics of SiC detectors subjected to extreme fluence of nuclear particles. <i>Semiconductors</i> , <b>2007</b> , 41, 115-119	0.7	6
269	Specific features of use of wide-gap semi-insulating materials for recording of nuclear radiation. <i>Semiconductors</i> , <b>2008</b> , 42, 1117-1121	0.7	6

268	Growth and Study of Thick 3C-SiC Epitaxial Layers Produced by Epitaxy on 6H-SiC Substrates. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 175-178	0.4	6
267	Semi-insulating silicon carbide layers obtained by diffusion of vanadium into porous 4H-SiC. <i>Semiconductors</i> , <b>2003</b> , 37, 594-597	0.7	6
266	Estimation of the energy characteristics of the 3C-SiC/2H-, 4H-, 6H-, and 8H-SiC heterojunctions. <i>Semiconductors</i> , <b>2005</b> , 39, 1391	0.7	6
265	Direct Experimental Comparison of the Effects of Electron Irradiation on the Charge Carrier Removal Rate in n-Type Silicon and Silicon Carbide. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 385-388	0.4	6
264	TEM (XHREM) and EDX Studies of 6H-SiC Porous Layer as a Substrate for Subsequent Homoepitaxial Growth. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 271-274	0.4	6
263	Structural defects in 6H-SiC substrates and their effect on the sublimation growth of epitaxial layers in vacuum. <i>Physics of the Solid State</i> , <b>2000</b> , 42, 1422-1426	0.8	6
262	Effect of the energy of recoil atoms on conductivity compensation in moderately doped n-Si and n-SiC under irradiation with MeV electrons and protons. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , <b>2016</b> , 384, 100-105	1.2	6
261	Optical Estimation of the Carrier Concentration and the Value of Strain in Monolayer Graphene Grown on 4H-SiC. <i>Semiconductors</i> , <b>2019</b> , 53, 1904-1909	0.7	6
260	High Quality Graphene Grown by Sublimation on 4H-SiC (0001). <i>Semiconductors</i> , <b>2018</b> , 52, 1882-1885	0.7	6
259	MoSe <sub>2</sub> /graphene/6H-SiC heterojunctions: energy band diagram and photodegradation. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 125007	1.8	5
258	Effect of high energy (15 MeV) proton irradiation on vertical power 4H-SiC MOSFETs. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 045004	1.8	5
257	Influence of the Proton Irradiation Temperature on the Characteristics of High-Power High-Voltage Silicon Carbide Schottky Diodes. <i>Technical Physics Letters</i> , <b>2020</b> , 46, 287-289	0.7	5
256	Metal-insulator transition in n-3C-SiC epitaxial films. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 023706	2.5	5
255	Isotopic heterogeneity in synthetic and natural silicon carbide. <i>Journal of Physics and Chemistry of Solids</i> , <b>2008</b> , 69, 2492-2498	3.9	5
254	DEEP LEVEL DEFECTS IN SILICON CARBIDE. <i>International Journal of High Speed Electronics and Systems</i> , <b>2006</b> , 16, 779-823	0.5	5
253	Estimates of the exciton transition energy in NH/3C/NH (N = 2, 4, 6, 8) heterostructures based on silicon carbide polytypes. <i>Semiconductors</i> , <b>2006</b> , 40, 549-553	0.7	5
252	Radiation Hardness of Silicon Carbide. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 957-960	0.4	5
251	The limiting energy resolution of SiC detectors in ion spectrometry. <i>Semiconductors</i> , <b>2005</b> , 39, 1420	0.7	5

250	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. <i>Carbon</i> , <b>2020</b> , 170, 666-676	10.4	5
249	Graphene on SiC Substrate as Biosensor: Theoretical Background, Preparation, and Characterization. <i>Materials</i> , <b>2021</b> , 14,	3.5	5
248	Impact of high temperature electron irradiation on characteristics of power SiC Schottky diodes. <i>Radiation Physics and Chemistry</i> , <b>2021</b> , 185, 109514	2.5	5
247	Radiation resistance of 4H-SiC Schottky diodes under irradiation with 0.9-MeV electrons. <i>Journal of Surface Investigation</i> , <b>2017</b> , 11, 924-926	0.5	4
246	A study of the effect of electron and proton irradiation on 4H-SiC device structures. <i>Technical Physics Letters</i> , <b>2017</b> , 43, 1027-1029	0.7	4
245	Fabrication of quasi-superlattices at the interface between 3C-SiC epitaxial layer and substrates of hexagonal SiC polytypes by sublimation epitaxy in vacuum. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 1156-1158	0.7	4
244	On the problem of the radiation hardness of SiC nuclear radiation detectors at high working temperatures. <i>Semiconductors</i> , <b>2011</b> , 45, 1369-1373	0.7	4
243	Electrical characteristics of multigraphene films grown on high-resistivity silicon carbide substrates. <i>Semiconductors</i> , <b>2010</b> , 44, 1389-1391	0.7	4
242	Role of spontaneous polarization in formation of heterojunctions from silicon carbide polytypes. <i>Semiconductors</i> , <b>2007</b> , 41, 297-300	0.7	4
241	Trap-recharging waves versus damped, forced charge-density oscillations in hexagonal silicon carbide. <i>European Physical Journal B</i> , <b>2007</b> , 60, 9-14	1.2	4
240	Effect of electron and proton irradiation on characteristics of SiC surface-barrier detectors of nuclear radiation. <i>Semiconductors</i> , <b>2008</b> , 42, 363-369	0.7	4
239	Carrier transport in a SiC detector subjected to extreme radiation doses. <i>Semiconductors</i> , <b>2006</b> , 40, 864-867	0.7	4
238	SiC Nuclear-Radiation Detectors. <i>Springer Series in Materials Science</i> , <b>2004</b> , 411-445	0.9	4
237	Characterization of 3C-SiC/6H-SiC Heterostructures Grown by Vacuum Sublimation. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 293-296	0.4	4
236	Investigation of the SiC Transistor and Diode Nuclear Detectors at 8 MeV Proton Irradiation. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 1025-1028	0.4	4
235	Thin Heavily Compensated 6H-SiC Epilayers as Nuclear Particle Detectors. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 763-768	0.4	4
234	Electron Traps in Undoped GaN Layers Subjected to Gamma-Irradiation and Annealing. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 799-802	0.4	4
233	Deep Centres Appearing in 6H and 4H SiC after Proton Irradiation. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 973-976	0.4	4



232	Effect of $\gamma$ irradiation on the photoluminescence kinetics of porous silicon. <i>Semiconductors</i> , <b>1999</b> , 33, 1315-1317	0.7	4
231	Minority Carrier Diffusion Length in Epitaxially Grown SiC(6H) pn Diodes. <i>Springer Proceedings in Physics</i> , <b>1992</b> , 269-273	0.2	4
230	Impact of 0.9 MeV electron irradiation on main properties of high voltage vertical power 4H-SiC MOSFETs. <i>Radiation Physics and Chemistry</i> , <b>2020</b> , 177, 109200	2.5	4
229	Effect of recoil atoms on radiation-defect formation in semiconductors under 100-MeV proton irradiation. <i>Journal of Surface Investigation</i> , <b>2016</b> , 10, 693-697	0.5	4
228	Long-term environmental impact of an oil spill in the southern part of Onega Bay, the White Sea. <i>Russian Journal of Marine Biology</i> , <b>2016</b> , 42, 205-215	0.7	4
227	Kelvin probe microscopy of MoSe <sub>2</sub> monolayers on graphene. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 1124, 081031	0.3	4
226	Optical and electrical properties of the MoSe <sub>2</sub> /graphene heterostructures. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 1092, 012002	0.3	4
225	Effect of Neutron Irradiation on Current-Voltage Characteristics of Packaged Diodes Based on 6H-SiC pn Structures. <i>Materials Science Forum</i> , <b>2017</b> , 897, 459-462	0.4	3
224	A Model of a Surface Dimer in the Problem of Adsorption. <i>Technical Physics Letters</i> , <b>2019</b> , 45, 461-463	0.7	3
223	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. <i>Crystals</i> , <b>2019</b> , 9, 115	2.3	3
222	Radiation Resistance of Devices Based on SiC. <i>Journal of Surface Investigation</i> , <b>2018</b> , 12, 364-369	0.5	3
221	Comparison of the Effects of Electron and Proton Irradiation on 4H-SiC and Si Device Structures. <i>Materials Science Forum</i> , <b>2018</b> , 924, 217-220	0.4	3
220	Low-Temperature Annealing of Lightly Doped n-4H-SiC Layers after Irradiation with Fast Electrons. <i>Semiconductors</i> , <b>2019</b> , 53, 975-978	0.7	3
219	Variant of Excess Current in 4H-SiC pn Structures. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 859-862	0.4	3
218	Radiation hardness of a wide-bandgap material by the example of SiC nuclear radiation detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2012</b> , 675, 20-23	1.2	3
217	Investigation of the transition layer in 3C-SiC/6H-SiC heterostructures. <i>Semiconductors</i> , <b>2013</b> , 47, 1539-1543	1.7	3
216	Effect of the energy of bombarding electrons on the conductivity of n-4H-SiC (CVD) epitaxial layers. <i>Semiconductors</i> , <b>2017</b> , 51, 299-304	0.7	3
215	A study of the intermediate layer in 3C-SiC/6H-SiC heterostructures. <i>Journal of Crystal Growth</i> , <b>2014</b> , 396, 100-103	1.6	3

214	Low-Temperature Transport Properties of Graphene and Multilayer Graphene on 6H-SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 137-140	0.4	3
213	Vacancy model of micropipe annihilation in epitaxial silicon carbide layers. <i>Semiconductors</i> , <b>2011</b> , 45, 727-730	0.7	3
212	4H-SiC Nuclear Radiation p-n Detectors for Operation up to Temperature 375 °C. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 849-852	0.4	3
211	Far-Action Radiation Defects and Gettering Effects in 4H-SiC Implanted with Al Ions. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 473-476	0.4	3
210	Effect of microwave treatment on current flow mechanisms in Au-TiBx-Al-Ti-n+-n+-GaN-Al2O3 ohmic contacts. <i>Semiconductors</i> , <b>2010</b> , 44, 745-751	0.7	3
209	Energy characteristics of SiC(0001)-intercalated hydrogen-graphene system. <i>Technical Physics Letters</i> , <b>2010</b> , 36, 856-858	0.7	3
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206	The Influence of the Extreme Fluences of 8 MeV Protons on Characteristics of SiC Nuclear Detectors Produced by Al Implantation. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 961-964	0.4	3
205	Temperature Dependence of the Band-Edge Injection Electroluminescence of 3C-SiC pn Structure. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 427-430	0.4	3
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199	Investigation of the p EBC-SiC/n +-6H-SiC heterostructures with modulated doping. <i>Technical Physics Letters</i> , <b>2002</b> , 28, 1011-1014	0.7	3
198	3C-SiC p-n structures grown by sublimation on 6H-SiC substrates. <i>Semiconductors</i> , <b>2003</b> , 37, 482-484	0.7	3
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194	Epitaxial 6H-SiC Layers as Detectors of Nuclear Particles. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 1447-1452	0.4	3
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189	Radiation-Induced Damage of Silicon-Carbide Diodes by High-Energy Particles. <i>Semiconductors</i> , <b>2018</b> , 52, 1758-1762	0.7	3
188	Radiation Hardness of Silicon Carbide upon High-Temperature Electron and Proton Irradiation. <i>Materials</i> , <b>2021</b> , 14,	3.5	3
187	Effect of high temperature irradiation with 15 MeV protons on characteristics of power SiC Schottky diodes. <i>Solid-State Electronics</i> , <b>2021</b> , 181-182, 108009	1.7	3
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185	Radiation hardness of n-GaN schottky diodes. <i>Semiconductors</i> , <b>2015</b> , 49, 1341-1343	0.7	2
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173	Annealing of radiation-compensated silicon carbide. <i>Technical Physics Letters</i> , <b>2012</b> , 38, 910-912	0.7	2
172	Heteroepitaxial Growth of 3C-SiC on Polar Faces of 6H-SiC Substrates, TEM Investigations. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 267-270	0.4	2
171	Conductivity compensation in p-6H-SiC in irradiation with 8-MeV protons. <i>Semiconductors</i> , <b>2011</b> , 45, 1145-1147	1.2	2
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165	Investigation of the parameters of deep centers in n-6HSiC epitaxial layers obtained by gas-phase epitaxy. <i>Semiconductors</i> , <b>1997</b> , 31, 896-898	0.7	2
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160	X-Ray Imaging and TEM Study of Micropipes Related to their Propagation through Porous SiC Layer/SiC Epilayer Interface. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 363-366	0.4	2
159	Electroluminescence of p-3C-SiC/n-6H-SiC Heterodiodes, Grown by Sublimation Epitaxy in Vacuum. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 597-600	0.4	2
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150	Wannier-Stark Localization Effects in 6H-SiC JFETs. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 873-876	0.4	2
149	Triode structure of ion detector based on 6H-SiC epitaxial films. <i>Applied Surface Science</i> , <b>2001</b> , 184, 455-469		2
148	Radiation hardness of SiC ion detectors under relativistic protons. <i>Semiconductors</i> , <b>2001</b> , 35, 481-484	0.7	2
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145	6H-SiC Diodes with Cellular Structure to Avoid Micropipe Effects. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 1355-1358	0.4	2
144	6H-SiC Schottky Barrier Diodes with Nearly Ideal Breakdown Voltage. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 1219-1222	0.4	2
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131	Electrochemical Treatment of Graphene. <i>Key Engineering Materials</i> , <b>2019</b> , 799, 197-202	0.4	1
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128	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 215302	2.5	1
127	Effect of Proton and Electron Irradiation on Current-Voltage Characteristics of Rectifying Diodes Based on 4H-SiC Structures with Schottky Barrier. <i>Materials Science Forum</i> , <b>2020</b> , 1004, 1081-1087	0.4	1
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125	Comparison of graphene films grown on 6H-SiC and 4H-SiC substrates. <i>Fullerenes Nanotubes and Carbon Nanostructures</i> , <b>2020</b> , 28, 321-324	1.8	1

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103	SiC Heteropolytype Structures Grown by Sublimation Epitaxy. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 161-166	0.4	1
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101	Synthesis and structural characterization of a heterocomposition based on porous layers of SiC polytypes. <i>Technical Physics Letters</i> , <b>2004</b> , 30, 950-953	0.7	1
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